

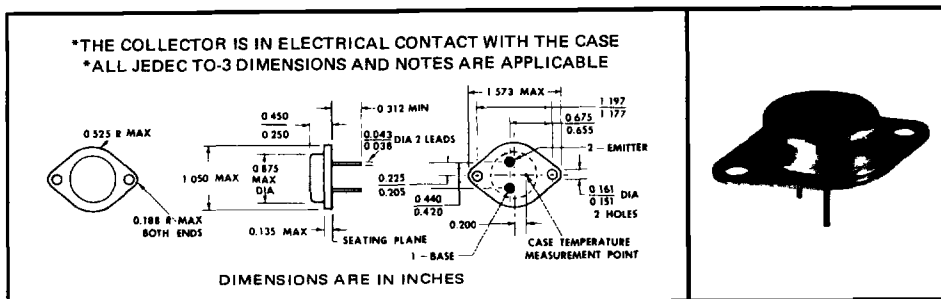
TYPES 2N1529 THRU 2N1548 P-N-P ALLOY-JUNCTION GERMANIUM POWER TRANSISTORS

TYPES 2N1529 THRU 2N1548
BULLETIN NO. DL-5 68109719, NOVEMBER 1968

FOR HIGH-POWER SWITCHING AND AMPLIFIER APPLICATIONS

mechanical data

These transistors are in precision welded, hermetically sealed enclosures. The mounting base provides an excellent heat path from the collector junction to a heat sink. The mounting base and heat sink must be in intimate contact for maximum heat transfer. Extreme cleanliness and the absence of flux during the assembly process prevents sealed-in contamination.



6

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	2N1529	2N1530	2N1531	2N1532	2N1533
Collector-Base Voltage	-40 V*	-60 V*	-80 V*	-100 V*	-120 V*
Collector-Emitter Voltage (See Note 1)	-30 V*	-45 V*	-60 V*	-75 V*	-90 V*
Emitter-Base Voltage	-20 V*	-30 V*	-40 V*	-50 V*	-60 V*
Continuous Collector Current	←		-5 A*	→	
Continuous Emitter Current	←		5 A*	→	
Continuous Device Dissipation at (or below) 25°C Case Temperature (See Note 2)	←		106 W	→	
Operating Collector Junction Temperature	←		{ 100°C* }	→	
			{ 110°C† }		
Storage Temperature Range	←		-65°C to 100°C*	→	

NOTES: 1. This value applies when base-emitter diode is short-circuited.
2. Derate linearly to 110°C case temperature at the rate of 1.25 W/deg.

*Indicates JEDEC registered data
†This value is guaranteed by Texas Instruments in addition to the JEDEC registered value which is also shown.

TYPES 2N1529 THRU 2N1548

P-N-P ALLOY-JUNCTION GERMANIUM POWER TRANSISTORS

2N1529 THRU 2N1533

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TYPE	MIN	MAX	UNIT
*V _{(BR)CEO} Collector-Emitter Breakdown Voltage	I _C = -500 mA, I _B = 0	2N1529	-20		V
		2N1530	-30		
		2N1531	-40		
		2N1532	-50		
		2N1533	-60		
*V _{(BR)CES} Collector-Emitter Breakdown Voltage	I _C = -500 mA, V _{BE} = 0	2N1529	-30		V
		2N1530	-45		
		2N1531	-60		
		2N1532	-75		
		2N1533	-90		
*V _{(BR)EBO} Emitter-Base Breakdown Voltage	I _E = -25 mA, I _C = 0	2N1529	-20		V
		2N1530	-30		
		2N1531	-40		
		2N1532	-50		
		2N1533	-60		
*I _{CBO} Collector Cutoff Current	V _{CB} = -2 V, I _E = 0	All		-200	μA
*I _{CBO} Collector Cutoff Current	V _{CB} = -25 V V _{CB} = -40 V V _{CB} = -55 V V _{CB} = -65 V V _{CB} = -80 V	I _E = 0	2N1529		mA
			2N1530		
			2N1531	-2	
			2N1532		
			2N1533		
*I _{CBO} Collector Cutoff Current	V _{CB} = -40 V V _{CB} = -60 V V _{CB} = -80 V V _{CB} = -100 V V _{CB} = -120 V	I _E = 0	2N1529		mA
			2N1530		
			2N1531	-20	
			2N1532		
			2N1533		
*I _{CBO} Collector Cutoff Current	V _{CB} = -15 V V _{CB} = -22.5 V V _{CB} = -30 V V _{CB} = -37.5 V V _{CB} = -45 V	I _E = 0, T _C = 90°C	2N1529		mA
			2N1530		
			2N1531	-20	
			2N1532		
			2N1533		
*I _{CEV} Collector Cutoff Current	V _{CE} = -40 V V _{CE} = -60 V V _{CE} = -80 V V _{CE} = -100 V V _{CE} = -120 V	V _{BE} = 1 V	2N1529		mA
			2N1530		
			2N1531	-20	
			2N1532		
			2N1533		
*I _{EBO} Emitter Cutoff Current	V _{EB} = -12 V, I _C = 0	All		-0.5	mA
*h _{FE} Static Forward Current Transfer Ratio	V _{CE} = -2 V, I _C = -3 A	All	20	40	
*g _{FE} Static Common-Emitter Forward Transfer Conductance	V _{CE} = -2 V, I _C = -3 A	All	1.2		mho
*V _{BE} Base-Emitter Voltage	I _B = -300 mA, I _C = -3 A	All		-1.7	V
*V _{CE(sat)} Collector-Emitter Saturation Voltage	I _B = -300 mA, I _C = -3 A	All		-1.5	V
*f _{hfo} Common-Emitter Forward Current Transfer Ratio Cutoff Frequency	V _{CE} = -2 V, I _C = -3 A	All	2		kHz
f _T Transition Frequency	V _{CE} = -2 V, I _C = -1 A, See Note 4	All	200		kHz

thermal characteristics

PARAMETER	TYPE	MAX	UNIT
*θ _{J-C} Junction-to-Case Thermal Resistance	All	0.6	deg/W

NOTE: 4. To obtain f_T, the |h_{re}| response with frequency is extrapolated at the rate of -6 dB/octave from f = 100 kHz to the frequency at which |h_{re}| = 1.

*Indicates JEDEC registered data

6

TYPES 2N1529 THRU 2N1548

P-N-P ALLOY-JUNCTION GERMANIUM POWER TRANSISTORS

2N1534 THRU 2N1538

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TYPE	MIN	MAX	UNIT
*V _{(BR)CEO} Collector-Emitter Breakdown Voltage	I _C = -500 mA, I _B = 0	2N1534 2N1535 2N1536 2N1537 2N1538	-20 -30 -40 -50 -60		V
*V _{(BR)CES} Collector-Emitter Breakdown Voltage	I _C = -500 mA, V _{BE} = 0	2N1534 2N1535 2N1536 2N1537 2N1538	-30 -45 -60 -75 -90		V
*V _{(BR)EBO} Emitter-Base Breakdown Voltage	I _E = -25 mA, I _C = 0	2N1534 2N1535 2N1536 2N1537 2N1538	-20 -30 -40 -50 -60		V
*I _{CB0} Collector Cutoff Current	V _{CB} = -2 V, I _E = 0	All		-200	μA
*I _{CB0} Collector Cutoff Current	V _{CB} = -25 V V _{CB} = -40 V V _{CB} = -55 V V _{CB} = -65 V V _{CB} = -80 V I _E = 0	2N1534 2N1535 2N1536 2N1537 2N1538		-2	mA
*I _{CB0} Collector Cutoff Current	V _{CB} = -40 V V _{CB} = -60 V V _{CB} = -80 V V _{CB} = -100 V V _{CB} = -120 V I _E = 0	2N1534 2N1535 2N1536 2N1537 2N1538		-20	mA
*I _{CB0} Collector Cutoff Current	V _{CB} = -15 V V _{CB} = -22.5 V V _{CB} = -30 V V _{CB} = -37.5 V V _{CB} = -45 V I _E = 0, T _C = 90°C	2N1534 2N1535 2N1536 2N1537 2N1538		-20	mA
*I _{CEV} Collector Cutoff Current	V _{CE} = -40 V V _{CE} = -60 V V _{CE} = -80 V V _{CE} = -100 V V _{CE} = -120 V V _{BE} = 1 V	2N1534 2N1535 2N1536 2N1537 2N1538		-20	mA
*I _{EBO} Emitter Cutoff Current	V _{EB} = -12 V, I _C = 0	All		-0.5	mA
*h _{FE} Static Forward Current Transfer Ratio	V _{CE} = -2 V, I _C = -3 A	All	35	70	
*g _{FE} Static Common-Emitter Forward Transfer Conductance	V _{CE} = -2 V, I _C = -3 A	All	1.5		mho
*V _{BE} Base-Emitter Voltage	I _B = -300 mA, I _C = -3 A	All		-1.5	V
*V _{CE(sat)} Collector-Emitter Saturation Voltage	I _B = -300 mA, I _C = -3 A	All		-1.2	V
*f _{hfe} Common-Emitter Forward Current Transfer Ratio Cutoff Frequency	V _{CE} = -2 V, I _C = -3 A	All	2		kHz
f _T Transition Frequency	V _{CE} = -2 V, I _C = -1 A, See Note 4	All	200		kHz

6

thermal characteristics

PARAMETER	TYPE	MAX	UNIT
*θ _{J-C} Junction-to-Case Thermal Resistance	All	0.8	deg/W

NOTE: 4. To obtain f_T, the |h_{FE}| response with frequency is extrapolated at the rate of -6 dB/octave from f = 100 kHz to the frequency at which |h_{FE}| = 1.

*Indicates JEDEC registered data

TYPES 2N1529 THRU 2N1548

P-N-P ALLOY-JUNCTION GERMANIUM POWER TRANSISTORS

2N1539 THRU 2N1543

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS		TYPE	MIN	MAX	UNIT
*V _{(BR)CEO} Collector-Emitter Breakdown Voltage	I _C = -500 mA, I _B = 0		2N1539 2N1540 2N1541 2N1542 2N1543	-20 -30 -40 -50 -60		V
*V _{(BR)CES} Collector-Emitter Breakdown Voltage	I _C = -500 mA, V _{BE} = 0		2N1539 2N1540 2N1541 2N1542 2N1543	-30 -45 -60 -75 -90		V
*V _{(BR)EBO} Emitter-Base Breakdown Voltage	I _E = -25 mA, I _C = 0		2N1539 2N1540 2N1541 2N1542 2N1543	-20 -30 -40 -50 -60		V
*I _{CBO} Collector Cutoff Current	V _{CB} = -2 V, I _E = 0		All		-200	μA
*I _{CBO} Collector Cutoff Current	V _{CB} = -25 V V _{CB} = -40 V V _{CB} = -55 V V _{CB} = -65 V V _{CB} = -80 V	I _E = 0	2N1539 2N1540 2N1541 2N1542 2N1543		-2	mA
*I _{CBO} Collector Cutoff Current	V _{CB} = -40 V V _{CB} = -60 V V _{CB} = -80 V V _{CB} = -100 V V _{CB} = -120 V	I _E = 0	2N1539 2N1540 2N1541 2N1542 2N1543		-20	mA
*I _{CBO} Collector Cutoff Current	V _{CB} = -15 V V _{CB} = -22.5 V V _{CB} = -30 V V _{CB} = -37.5 V V _{CB} = -45 V	I _E = 0, T _C = 90°C	2N1539 2N1540 2N1541 2N1542 2N1543		-20	mA
*I _{CEV} Collector Cutoff Current	V _{CE} = -40 V V _{CE} = -60 V V _{CE} = -80 V V _{CE} = -100 V V _{CE} = -120 V	V _{BE} = 1 V	2N1539 2N1540 2N1541 2N1542 2N1543		-20	mA
*I _{EBO} Emitter Cutoff Current	V _{EB} = -12 V, I _C = 0		All		-0.5	mA
*h _{FE} Static Forward Current Transfer Ratio	V _{CE} = -2 V, I _C = -3 A		All	50	100	
*g _{FE} Static Common-Emitter Forward Transfer Conductance	V _{CE} = -2 V, I _C = -3 A		All	3		mho
*V _{BE} Base-Emitter Voltage	I _B = -300 mA, I _C = -3 A		All		-0.7	V
*V _{CE(sat)} Collector-Emitter Saturation Voltage	I _B = -300 mA, I _C = -3 A		All		-0.3	V
*f _{inf} Common-Emitter Forward Current Transfer Ratio Cutoff Frequency	V _{CE} = -2 V, I _C = -5 A		All	1		kHz
f _T Transition Frequency	V _{CE} = -2 V, I _C = -1 A, See Note 4		All	200		kHz

thermal characteristics

PARAMETER	TYPE	MAX	UNIT
*θ _{J-C} Junction-to-Case Thermal Resistance	All	0.8	deg/W

NOTE: 4. To obtain f_T, the |h_{re}| response with frequency is extrapolated at the rate of -6 dB/octave from f = 100 kHz to the frequency at which |h_{re}| = 1.

*Indicates JEDEC registered data.

TYPES 2N1529 THRU 2N1548

P-N-P ALLOY-JUNCTION GERMANIUM POWER TRANSISTORS

2N1544 THRU 2N1548

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TYPE	MIN	MAX	UNIT	
*V _{(BR)CEO} Collector-Emitter Breakdown Voltage	I _C = -500 mA, I _B = 0	2N1544	-20		V	
		2N1545	-30			
		2N1546	-40			
		2N1547	-50			
		2N1548	-60			
*V _{(BR)CES} Collector-Emitter Breakdown Voltage	I _C = -500 mA, V _{BE} = 0	2N1544	-30		V	
		2N1545	-45			
		2N1546	-60			
		2N1547	-75			
		2N1548	-90			
*V _{(BR)EBO} Emitter-Base Breakdown Voltage	I _E = -20 mA, I _C = 0	2N1544	-20		V	
		2N1545	-30			
		2N1546	-40			
		2N1547	-50			
		2N1548	-60			
*I _{CEO} Collector Cutoff Current	V _{CB} = -2 V, I _E = 0	All		-200	μA	
*I _{CEO} Collector Cutoff Current	I _E = 0	V _{CB} = -25 V	2N1544		-2	mA
		V _{CB} = -40 V	2N1545			
		V _{CB} = -55 V	2N1546			
		V _{CB} = -65 V	2N1547			
		V _{CB} = -80 V	2N1548			
*I _{CEO} Collector Cutoff Current	I _E = 0	V _{CB} = -40 V	2N1544		-20	mA
		V _{CB} = -60 V	2N1545			
		V _{CB} = -80 V	2N1546			
		V _{CB} = -100 V	2N1547			
		V _{CB} = -120 V	2N1548			
*I _{CEO} Collector Cutoff Current	I _E = 0, T _C = 90°C	V _{CB} = -15 V	2N1544		-20	mA
		V _{CB} = -22.5 V	2N1545			
		V _{CB} = -30 V	2N1546			
		V _{CB} = -37.5 V	2N1547			
		V _{CB} = -45 V	2N1548			
*I _{CEV} Collector Cutoff Current	V _{BE} = 1 V	V _{CE} = -40 V	2N1544		-20	mA
		V _{CE} = -60 V	2N1545			
		V _{CE} = -80 V	2N1546			
		V _{CE} = -100 V	2N1547			
		V _{CE} = -120 V	2N1548			
*I _{EBO} Emitter Cutoff Current	V _{EB} = -12 V, I _C = 0	All		-0.5	mA	
*h _{FE} Static Forward Current Transfer Ratio	V _{CE} = -2 V, I _C = -3 A	All	75	150		
*g _{FE} Static Common-Emitter Forward Transfer Conductance	V _{CE} = -2 V, I _C = -3 A	All	4		mho	
*V _{BE} Base-Emitter Voltage	I _B = -300 mA, I _C = -3 A	All		-0.6	V	
*V _{CE(sat)} Collector-Emitter Saturation Voltage	I _B = -300 mA, I _C = -3 A	All		-0.2	V	
*f _{hfe} Common-Emitter Forward Current Transfer Ratio Cutoff Frequency	V _{CE} = -2 V, I _C = -5 A	All	1		kHz	
f _T Transition Frequency	V _{CE} = -2 V, I _C = -1 A, See Note 4	All	200		kHz	

6

thermal characteristics

PARAMETER	TYPE	MAX	UNIT
*θ _{J-C} Junction-to-Case Thermal Resistance	All	0.8	deg/W

NOTE: 4. To obtain f_T, the |h_{fe}| response with frequency is extrapolated at the rate of -6 dB/octave from f = 100 kHz to the frequency at which |h_{fe}| = 1.
*Indicates JEDEC registered data

TYPES 2N1529 THRU 2N1548

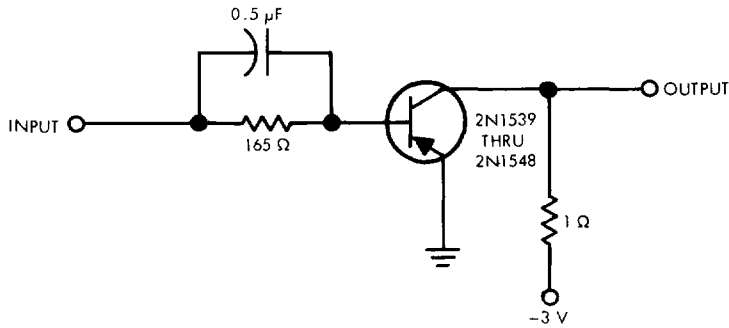
P-N-P ALLOY-JUNCTION GERMANIUM POWER TRANSISTORS

2N1539 THRU 2N1548

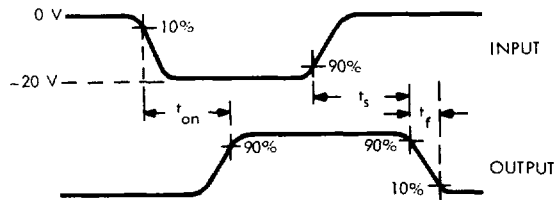
switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	TYP	UNIT
t_{on} Turn-On Time	$I_C \approx 3 \text{ A}$, $R_L = 1 \Omega$, See Figure 1	5	μs
t_s Storage Time		3	μs
t_f Fall Time		5	μs

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE WAVEFORMS

- NOTES: a. The input pulse is supplied by a generator with the following characteristics: $t_r \leq 0.1 \mu\text{s}$, $t_p = 50 \mu\text{s}$, duty cycle $\leq 10\%$.
 b. The waveforms are monitored on an oscilloscope with the following characteristics: $t_r \leq 0.1 \mu\text{s}$, $R_{in} \geq 100 \text{ k}\Omega$, $C_{in} \leq 20 \text{ pF}$.

FIGURE 1

TYPES 2N1529 THRU 2N1548 P-N-P ALLOY-JUNCTION GERMANIUM POWER TRANSISTORS

THERMAL INFORMATION

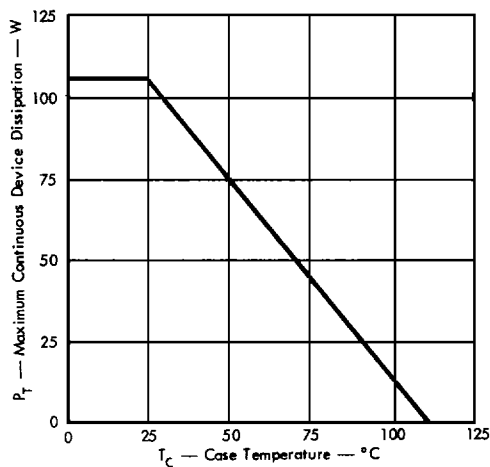


FIGURE 2

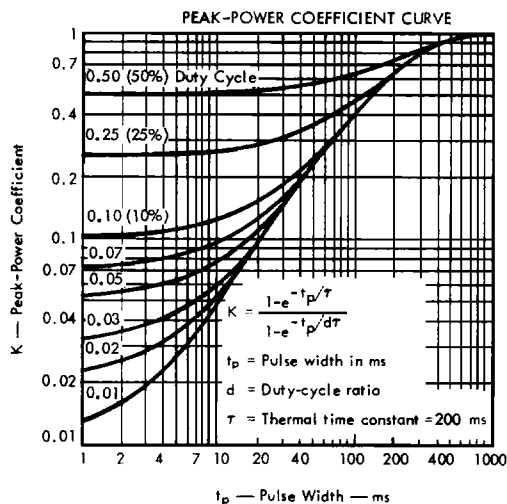


FIGURE 3

SYMBOL DEFINITION

SYMBOL	DEFINITION	VALUE	UNIT
P _{T(av)}	Average Power Dissipation		W
P _{T(max)}	Peak Power Dissipation		W
θ _{J-C}	Junction-to-Case Thermal Resistance	0.8	deg/W
θ _{C-HS}	Case-to-Heat-Sink Thermal Resistance		deg/W
θ _{HS-A}	Heat-Sink-to-Free-Air Thermal Resistance		deg/W
T _A	Free-Air Temperature		°C
T _C	Case Temperature		°C
T _{J(av)}	Average Junction Temperature	≤ 110	°C
T _{J(max)}	Peak Junction Temperature	≤ 110	°C
K	Peak-Power Coefficient	See Figure 3	
t _p	Pulse Width		ms
d	Duty-Cycle Ratio		

Equation No. 1 — Application: d-c power dissipation, heat sink used.

$$P_{T(av)} = \frac{T_{J(av)} - T_A}{\theta_{J-C} + \theta_{C-HS} + \theta_{HS-A}} \quad \text{for } 25^\circ\text{C} \leq T_C \leq 110^\circ\text{C} \quad \text{as in Figure 2}$$

Equation No. 2 — Application: Peak power dissipation, heat sink used.

$$P_{T(max)} = \frac{T_{J(max)} - T_A}{d(\theta_{C-HS} + \theta_{HS-A}) + K\theta_{J-C}} \quad \text{for } 25^\circ\text{C} \leq T_C \leq 110^\circ\text{C}$$

Example — Find P_{T(max)} (design limit)

OPERATING CONDITIONS:

$$\theta_{C-HS} + \theta_{HS-A} = 2.25 \text{ deg/W (From information supplied with heat sink.)}$$

$$T_{J(av)} \text{ (design limit)} = 110^\circ\text{C}$$

$$T_A = 50^\circ\text{C}$$

$$d = 10\% (0.1)$$

$$t_p = 10 \text{ ms}$$

Solution:

From Figure 3, Peak-Power Coefficient

$$K = 0.125 \text{ and by use of equation No. 2}$$

$$P_{T(max)} = \frac{T_{J(max)} - T_A}{d(\theta_{C-HS} + \theta_{HS-A}) + K\theta_{J-C}}$$

$$P_{T(max)} = \frac{110 - 50}{0.1(2.25) + 0.125(0.8)} = 184 \text{ W}$$